
2SC5461

Silicon NPN Triple Diffused
Character Display Horizontal Deflection Output

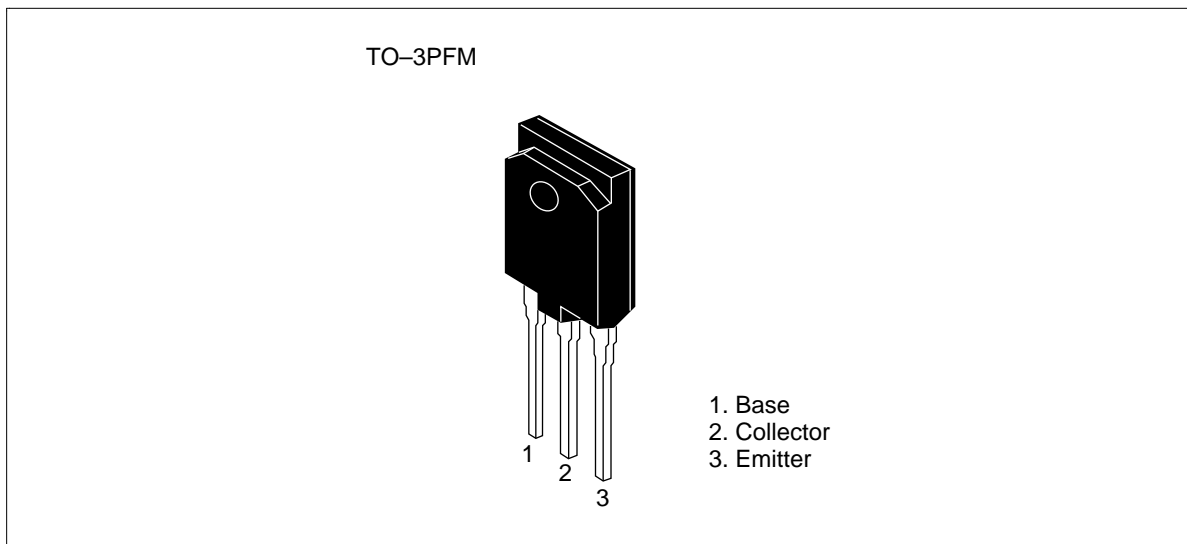
HITACHI

ADE-208-630 (Z)
1st. Edition
Oct. 1, 1998

Features

- High breakdown voltage
 $V_{CBO} = 1500 \text{ V}$
- High speed switching
 $t_f = 0.15 \mu\text{sec}(\text{typ.})$ at $f_H = 64\text{kHz}$
- Isolated package
TO-3PFM

Outline



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Absolute Maximum Ratings (Ta = 25°C)

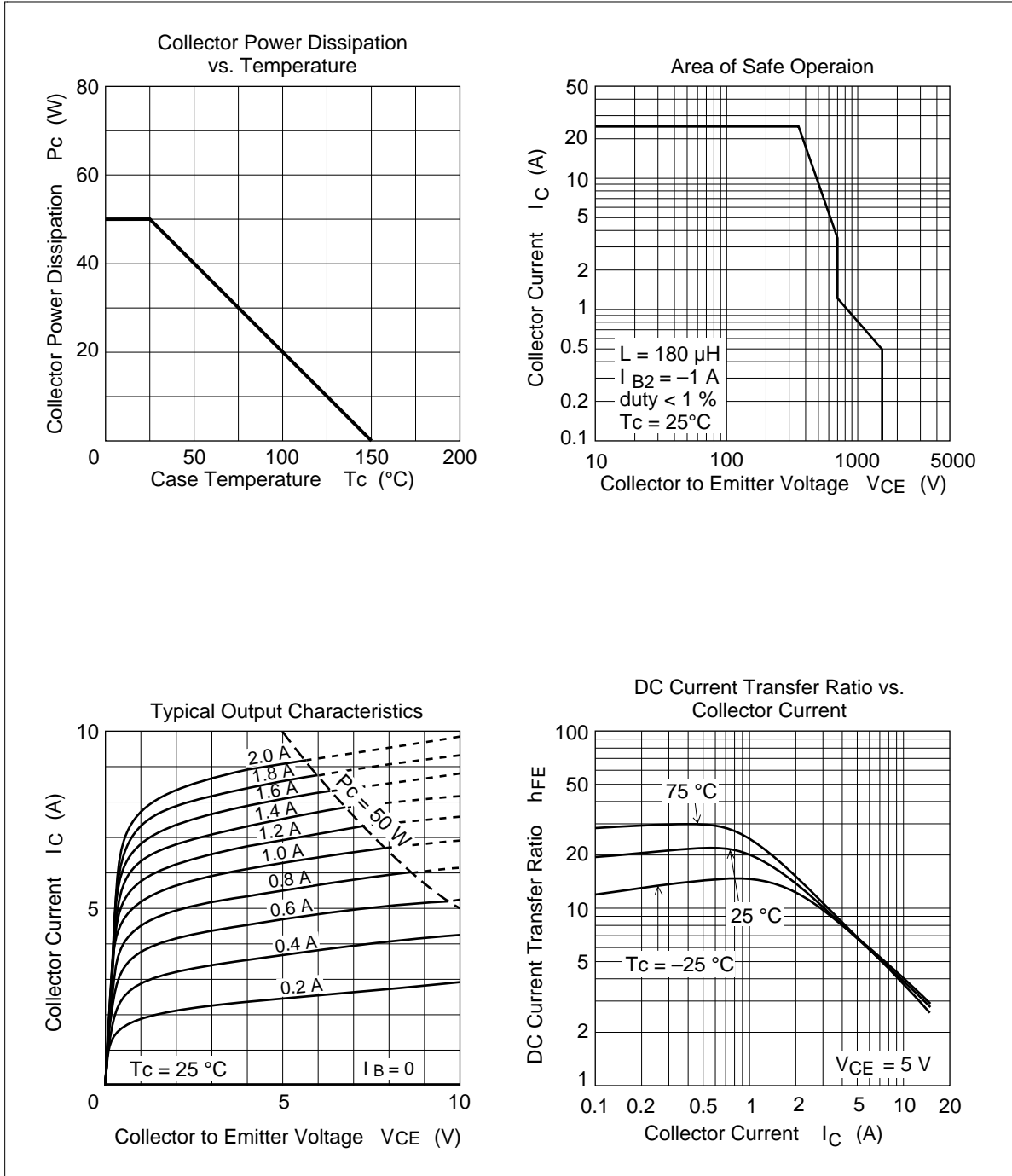
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	1500	V
Collector to emitter voltage	V_{CEO}	700	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	15	A
Collector peak current	$i_{c(peak)}$	30	A
Collector power dissipation	P_C ^{Note1}	50	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

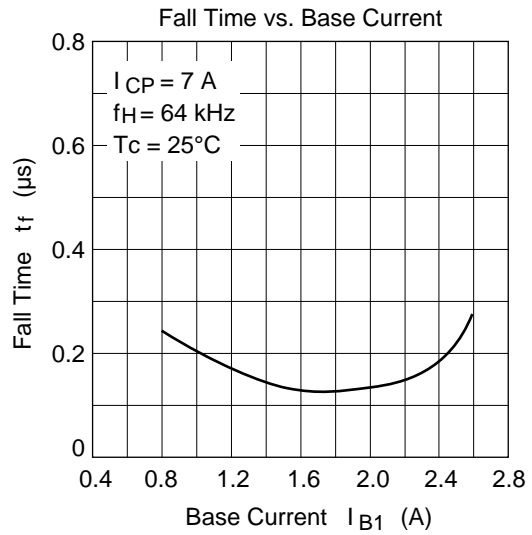
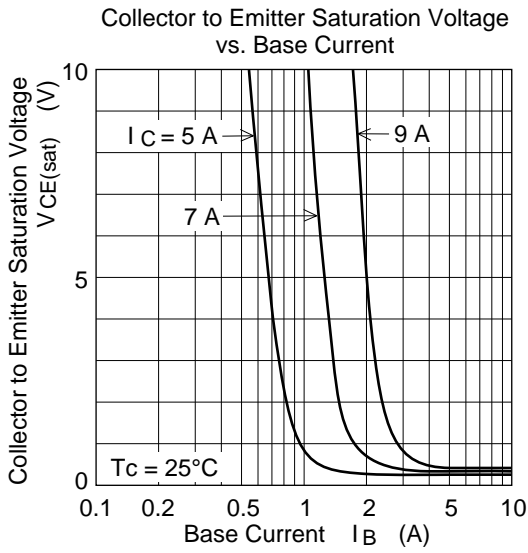
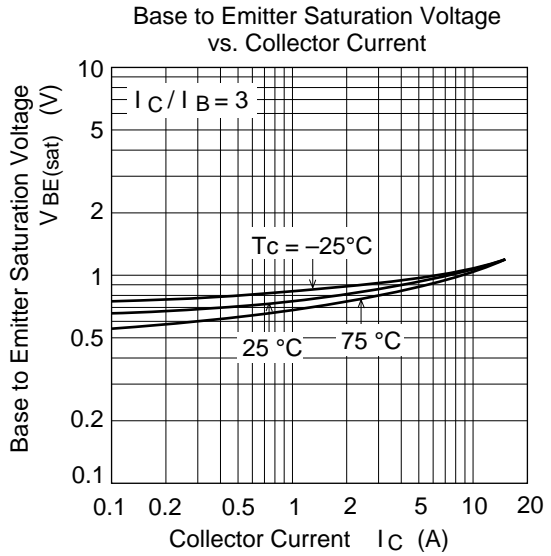
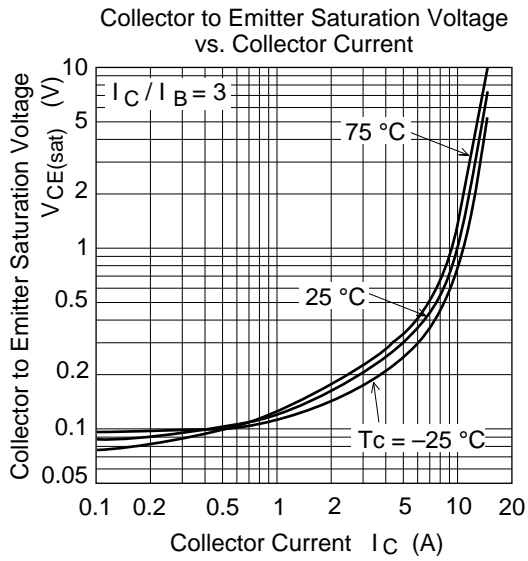
Note: 1. Value at $T_c = 25^\circ\text{C}$

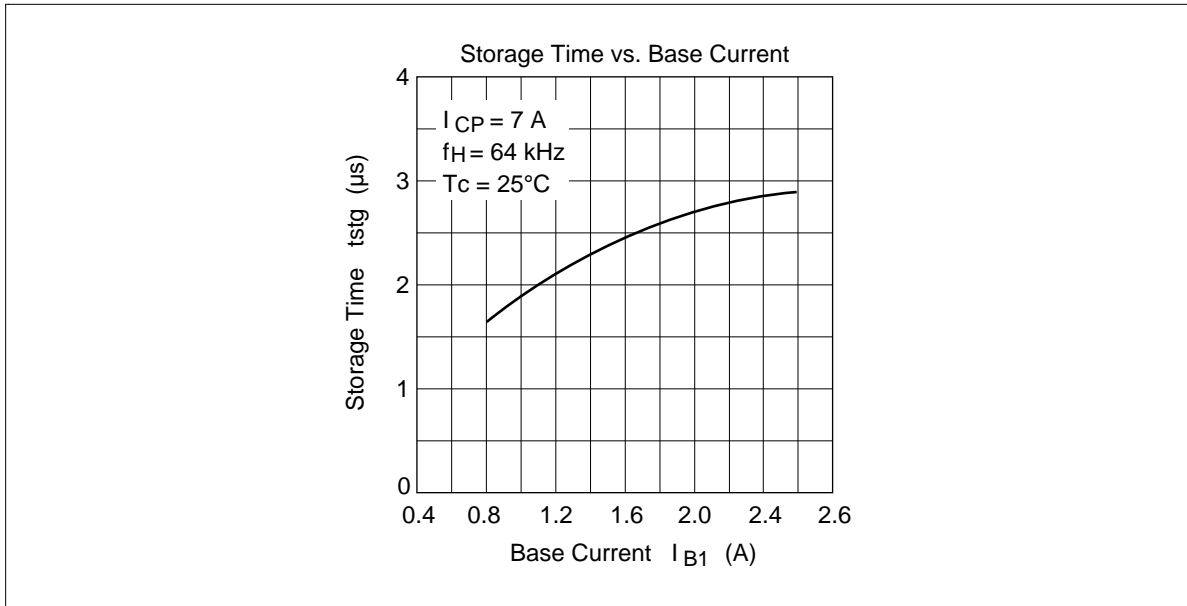
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	700	—	—	V	$I_C = 10\text{mA}$, $R_{BE} = \bullet$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10\text{mA}$, $I_C = 0$
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 1500\text{V}$, $R_{BE} = 0$
DC current transfer ratio	h_{FE1}	10	—	40		$V_{CE} = 5\text{V}$, $I_C = 1\text{A}$
DC current transfer ratio	h_{FE2}	3.5	—	6.5		$V_{CE} = 5\text{V}$, $I_C = 8\text{A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 10\text{A}$, $I_B = 3\text{A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 10\text{A}$, $I_B = 3\text{A}$
Fall time	t_f	—	0.2	0.4	μs	$I_{CP} = 7\text{A}$, $I_{B1} = 2.8\text{A}$ $f_H = 31.5\text{kHz}$
Fall time	t_f	—	0.15	—	μs	$I_{CP} = 7\text{A}$, $I_{B1} = 1.8\text{A}$ $f_H = 64\text{kHz}$

Main Characteristics

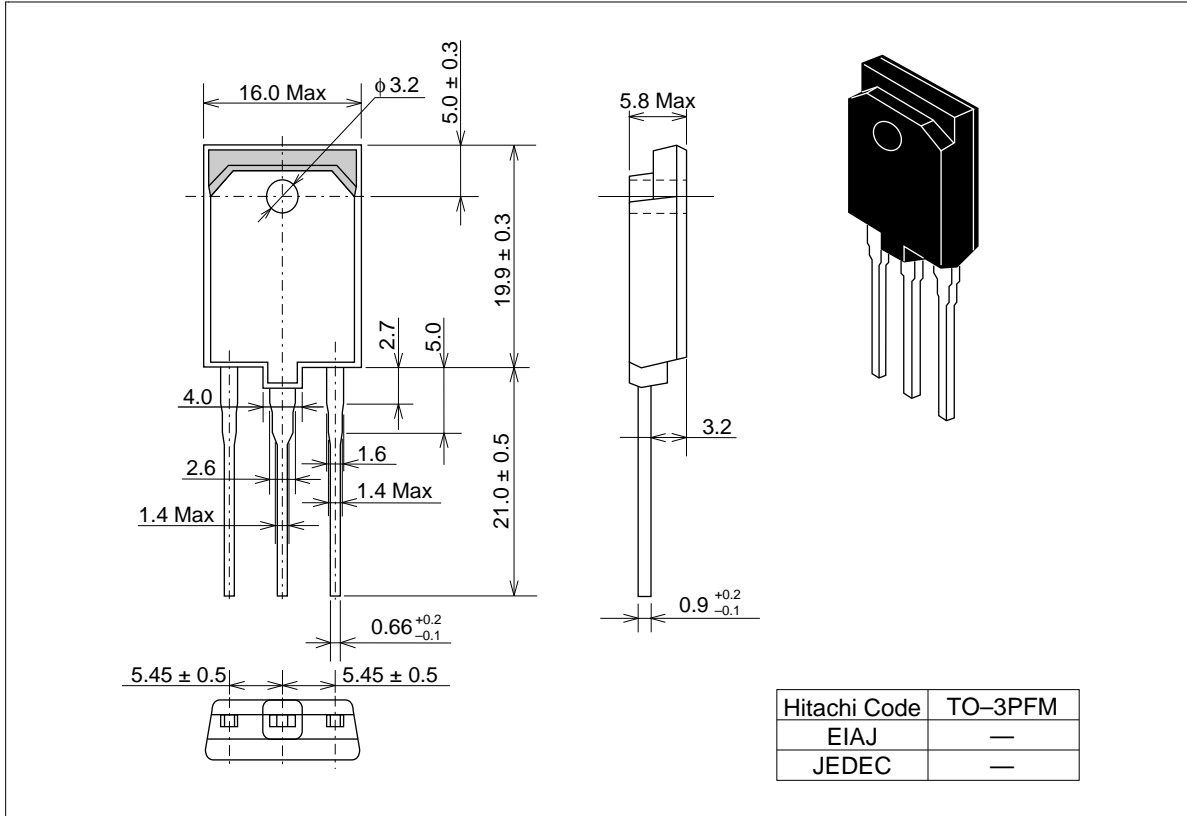






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Package Dimensions (Unit: mm)



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
Europe : <http://www.hitachi-eu.com/hel/ecg>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
2000 Sierra Point Parkway
Brisbane, CA 94005-1897
Tel: <1> (800) 285-1601
Fax: <1> (303) 297-0447

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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